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Substitute	e for form 1449A/	PTO		Complete if Known			
				Application Number	10/627,155		
INFO	RMATIO	N DIS	CLOSURE	Filing Date	7/24/03		
STAT	FMENT	BY A	PPLICANT	First Named Inventor	Patel		
017		•		Art Unit	Not Yet Assigned 7813		
(	(use as many sheets as necessary)			Examiner Name	Not Yet Assigned		
Sheet	1	of	6	Attorney Docket Number	P102-US		

			U.S. PAT	ENT DOCUMENTS	,
Examiner	Cite	Document Number	Publication Date	Name of Palentee or	Pages, Columns, Lines, Where
Ipitials		Number - Kind Coda <sup>2</sup> (if known		Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
FIV I		US- 3,511,727	05-12-1970	Hays, R.G.	
$\langle v, y \rangle$		US- 4,190,488	02-26-1980	Winters, H.F.	
211/2	• · ·	US- 4.310,380	12-12-1982	Flamm et al.	
WB.		US- 4,498,953	02-12-1985	Cook et al.	
SWI.		US- 6.051.503	04-18-2000	Bhardwai, J.K.	L
LN.L.	• • • • • • • • • • • • • • • • • • • •	US- 6.436.229	08-20-2002	Tai et al.	
W.		US- 6.162.367	12-19-2000	Tal et al.	
W.X.		US- 6.290.864 B1	09-18-2001	Patel et al.	
STWIL.		US- 6.355.181 B1	03-12-2002	McQuarrie, A.D.	
RWI.		US- 2001/0002663 A1	06-07-2001	Tai et al.	
LUI.		US- 5,439,553	08-08-1995	Grant et al.	
BWX.		US- 2002/0033229 A1	03-21-2002	Lebouitz et al.	
JW.X.		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
WJ.X.		US- 2003/0054588 A1	03-20-2003	Patel, et al.	
MI.		US- 5,726,480	03-10-1998	Pister, K.S.	
SINIX.		US- 2002/0185699 AI	12-12-2002	Reid	
ente.		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
が以		US- 5,835,256	11-10-1998	Huibers, A.	
KN.X		US- 2002/0047172 A1	04-25-2002	Reid	
W. 1 V	i	US- 2003/0166342 A1	09/04/03	Chinn, et al.	

		FORE	IGN PATENT D	OCUMENTS		
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document  County, Code 3 - Number 4 - Kind Code 5 (// known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pagas, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	76
なかよ		EP-0704884-A2	04-03-1996	Mehta, J.		
XWX.		EP-0822582-A2	02-04-1998	Bhardwal, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
YUX.	]	WO-99/49506	09-30-1999	McQuarrie, A.D.		.
IWI		EP-0878824-A2	11-18-1998	McQuarrie et al.		.
IXAX.X		EP-0878824-A3	01-19-2000	McQuarrie et al.		L_
XWI.		JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.	Abstract	.
XWX.		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.	Abstract_	.
XWX		JP-1985/60057938-A	04-03-1985	Katsumi et al.	Abstract	
IN.		WO-98/32163	07-23-1998	Tai et al.		<u> </u>

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control number. Complete if Known Substitute for form 1449A/PTO 10/627,155 **Application Number** INFORMATION DISCLOSURE 7/24/03 Filing Date Patel STATEMENT BY APPLICANT First Named Inventor Not Yol Assigned <u> 28/3</u> Art Unit (use as many sheets as necessary) Not Yet Assigned Examiner Name Attorney Docket Number P102-US of Sheet

			U.S. PAT	ENT DOCUMENTS	
Examiner		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant
initials	No. 1	Number - Kind Code <sup>1</sup> (if known	MM-DD-YYYY	Applicant of Cited Document	Figures Appear
Y/V/X		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
7W41		US. 6,396,619 B1	05-28-2002	Huibers, et al.	
W.S.		US- 6.576.489 B2	06/10/03	Leung, et a	
N.K.		us- 6,238,581	. 05-29-2001	Hawkins, et al.	
W.S.		US- 6,115.172	09-05-2000	Jeong	
SW.B.		US- 6.204.080	03-20-2001	Hwang	
W.X.		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
W.A.		US- 2002/0164879 A1	11/07/02	Leung, et al.	
17.8		US- 2002/0163051 A1	11/07/02	Gopal, et al.	
W.J.		US- 2003/0077878 A1	04/24/03	Kumar, et al.	,
SW.X.	•••	US- 6,197,610 B1	03/06/2001	Toda	
10,2		US- 6.500.356 B2	12/31/02	Goto, et al.	
WZ.		US- 2003/0124848 A1	0703/03	Chinn, et al.	
7W.X.		US- 2003/0219986 A1	11/27/03	Rattner, et al.,	
		US-			

	FOREIGN PATENT DOCUMENTS									
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document  Country Code 3 - Number 4 - Kind Code 4 (# knewn)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pagas, Columns, Lines, Where Relevant Pessages or Relevant Figures Appear	76				
IWX.		JP-1997/09251981-A	09-22-1997	Kazuaki et al.	Abstract					
IN.S		JP-1998/10313128-A	11-24-1998	Hanmin et al.	Abstract					
XUX		JP-1998/10317169-A	12-02-1998	McQuarrie et al.	Abstract					
XW.X.		JP-1986/61187238-A	08-20-1986	Nobuo et al.	Abstract					
INI		JP-1986/61270830-A	12-01-1986	Toru, T.	Abstract					
LWI		JP-1987/62071217-A	04-01-1987	Toru et al.	Abstract	L				
INI		JP-1988/63155713-A	06-28-1988	Tadashi, F.	Abstract					
XN/X		JP-1986/61053732-A	03-17-1986	Arata et el.	Abstract					
INI	Ī · · ·	JP-1986/61134019-A	06-21-1986	Shinji et al.	Abstract					
<b>X1.7.X</b>		JP-1986/61181131-A	08-13-1986	Shinii et al.	Abstract					

Examiner **Date** June 20, 2005 Signature Considered

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in

<sup>\*</sup>EXAMINER: Initial in reterence considered, whether or not citation is in conformance with MPEP obs. Draw line intrough citation is not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at <a href="www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 9 Applicant is to place a check mark here if English language Translation is attached.

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Examiner	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where	
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BW.		JP-1989/01208834-A	08-22-1989	Nobuo et al.	Abstract_
QUX.		JP-1989/10217921-A 01217921-A	08-31-1989	Tsuneo et al.	Abstract
又心文		JP-1990/02250323-A	10-08-1990	Susumu et al.	Abstract
KIUX.		JP-1991/03012921-A	01-21-1991	Nobuo et al.	Abstract
IWI.		JP-1992/04096222-A	03-27-1992	Atsuyuki, A.	Abstract
IXATI I		JP-1995/07029823-A	01-31-1995	Hiroshi, T.	Abstract
				l	<u> </u>

June 20, 2005 Date Examiner Considered

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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Complete if Known Substitute for form 1449B/PTO 10/627,155 **Application Number** INFORMATION DISCLOSURE 7/24/03 Filing Date First Named Inventor Patel STATEMENT BY APPLICANT Not Yet Assigned Group Art Unit Not Yet Assianed (use as many sheets as necessary) **Examiner Name** Attorney Docket Number P102-US of I Sheet

Examiner Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue	7
QNQ.	number(s), publisher, city and/or country where published  ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching In F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
2.W.2	GLIDEMEISTER, J.M., "Xenon Diffuoride Etching System" (Nov. 17, 1997).	
2,11,2	HABUKA at al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
2.W.L.	HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO2 Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
21,12	HOULE, F.A., "Dynamics of SiF4 Desorption During Etching of Silicon by XeF2", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
W.	FLAMM et al., "XeF2 and F-Atom Reactions with Si: Their Significance for Plasma Etching", Solid State Technol. 26, 117 (1983).	
21,),2	IBBOTSON et al., "Plasmaless Dry Etching of Sillcon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	-
2212	IBBOTSON et al., "Comparison of XeF2 and F-atom Reactions with Si and SiO2", Applied Physics Letter, Vol. 44, 1129 (1984).	
R.D.S.	STRELLER et al., "Selectivity in Dry Etching of Si (100) and XeF2 and VUV Light", Elsevier Science B.V., Applied Surface Science Vol. 106 (1996), pp. 341-346.	
&N.&.	VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
L.D.J.	WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol, B 1(4) (Oct/Dec 1983), pp. 927-931.	-

Date Examiner Considered Signature



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		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	Ţ²
S.W.S.		Kurl Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
808.		WINTERS et al., "The Etching of Silicon with XeF2 Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
		YACTIY, Inc., Marketing Brochure (June 27, 1999).	•
		*Xenen Billuorida Isovopio Etch System: Seeing is Believing*, Surface Technology Systems Ltd. brochure.  Newport, UK (date unknown).	
Z.W.S.		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
?.W.&.		BASSOM et al., "Modeling and Optimizing XeF2-enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
8.N.L		KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	
2.W.L.		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millanium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
\$1V.S.		CHANG et al., "Gas-Phase Silicon Micromachining with Stitcon Difluoride", Proceedings of the SPIE - The International Socity for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	
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Date Examiner

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	_	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS	
Examiner Initials	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	Т
J.W.L.		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted SVXeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
2.10,2		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
S.U.S		SUGANO et al., "Study on XeF2 Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechantronics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Triflueride", International Solid State Sensors and Actuators Conference (Transducers 97), Chicago, IL, Vol. 2 (June 18 - 19, 1997), pp. 1505-1508 (abstract only).	
2.22		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5-mu m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
l,N,L,		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	_
I.W. S.		SEBEL et al., "Etching of Si Through a Thick Condensed XeF2 Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	-
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Attorney Docket No. P102-US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Patel, et al.

Art Unit: Not Yet Assigned

Serial No.:

10/627,155

Examiner: Not Yet Assigned

Filed: 7/24/03

For:

A MICROMIRROR ARRAY DEVICE WITH SMALL PITCH SIZE

## INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-145

Sir:

The attention of the Patent and Trademark Office is hereby directed to the following documents:

serial number 10,627,302 to Patel, et al, filed July 24, 2003;

serial number 10,627,303 to Patel, et al, filed July 24, 2003;

The attention of the Patent and Trademark Office is hereby also directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

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INFORMATION DISCLOSURE			ATTY. DOCKET NO.		SERIAL NO.				
			P102-US	0/627,155	527,155				
MOV 2 9 20C4 1	PTO-1449		APPLICANT Patel, et al						
SHEET 1 OF 1			FILING DATE 7/24/03	ROUP 28	DUP 2813				
CA INTO			ATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLAS	S SUBCLASS	FILING DATE			
	5,835,256	11/10/98	Hulbers						
S.W.L.	6,046,840	04/04/00	Huibers						
21,2,	6,529,310	03/04/03	Huibers, et al.						
A 7.0 1.0 .	6,396,619	05/28/02	Hulbers, et al.						
	6,523,961	02/25/03	Ilkov, et al.						
	2003/0054588	03/20/03	Patel, et al.						
21/12.	2004/0125346	07/01/04	Huibers	_					
1112	2002/0132389	09/19/02	Patel, et al.						
70,70									
		FOREIG	N PATENT DOCUMENT	S					
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLAS	S SUBCLASS	TRANSLATION			
						YES	NO		
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	OTHER DOCU	MENTS (Incl	uding Author, Title, Date,	Pertine	nt Pages, Etc.)				
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NFORMATION DISCLOSURE CITATION PTO-1449			ATTY. DOCKET NO. SER			IAL NO.			
			P102-US 10/627,155						
			APPLICANT Patel, et al						
			FILING DATE 7/24/03		GRO	OUP Not Yet Assigned 2813			
		U.S. I	PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CL	ASS	SUBCLASS	FILING	G DATE	
S.W.L.	2003/0160540	8/28/03	Miller, et al.						
I.W.L.	6,819,470	11/16/04	Meier, et al.	-					
R.W.R.	2003/0117688	6/26/03	Meier, et al.	Ţ -					
811.8.	2003/0117686	6/26/03	DiCarlo	_					
211.2.	2002/0093721	7/18/02	Knipe	-					
A 100 (A)	6,724,518	4/20/04	Meyer, et al.						
SWI.	6,147,790	11/14/00	Meier, et al.	-					
IN. I.	6,285,490	9/4/01	Meier, et al.	_					
S.W.S.	6,523,961	2/25/03	llkov, et al.	-					
S.W.S.	2002/0024641	2/28/02	Ilkov, et al.	T					
l.W.S.	2004/0004753	1/8/04	Pan	<u> </u>					
<del>V</del>		FOREIC	ON PATENT DOCUMENT	rs					
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS		SUBCLASS	TRANSLATION		
				ļ	******		YES	NO	
SNIS.	WO 2004/001487	12/13/03	PCT						
\$N.S.	WO 2004/000720	12/13/03	РСТ	_	_				
SW.L.	WO 2004/001717	12/13/03	РСТ		_		<u></u>		
	OTHER DOCU	MENTS (Inc	cluding Author, Title, Date,	Perti	nent I	Pages, Etc.)	<del></del>		
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-	А								
EXAMINER A	PostQue (2)	Smoot	DATE CONSIDERED	Ju	ne.	20. 2	005		